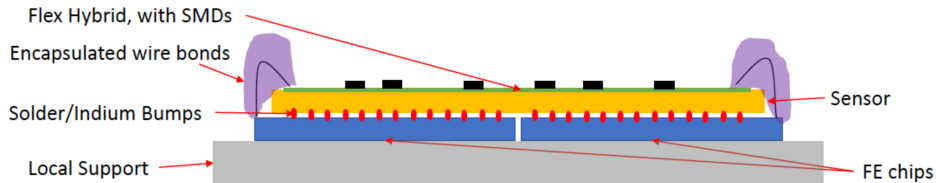


MAPS

Lingxin Meng

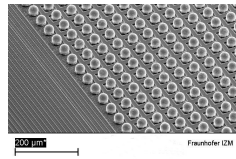
Weekly Instrumentation Meeting LBNL
03 November 2023

- Traditional pixel detectors are **hybrid** pixel detectors, e.g. the current ATLAS Inner Detector or Inner Tracker upgrade
- Sensor: high resistivity silicon wafer, single-sided (ITk) or double-sided (IBL) process
- Frontend: low resistivity CMOS readout chip using commercial process, e.g. RD53 chips with TSMC 65 nm
- Hybridisation process: flip-chip and DC-couple sensor pixels to FE pixels
- Need 3 – 4 vendors incl. subcontractors: sensor, FE chip, hybridisation (dicing, bump deposition, flip-chipping)



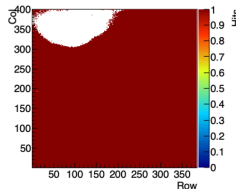
Pros

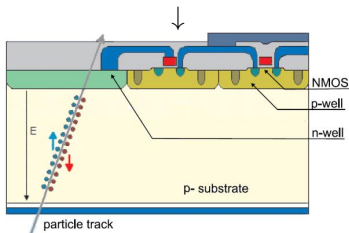
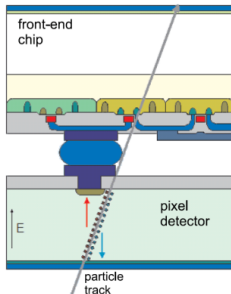
- High resistive sensors are radiation hard, at least up to $5e15$ and $2e16$ $1 \text{ MeV } n_{\text{eq}}/\text{cm}^2$ for planar and 3D
- Independent vendor choices for each component, e.g. 3 different planar sensor vendors for ITk, several hybridisation vendors - eggs in baskets



Cons

- Generally expensive due to a high number of components and vendors, high resistivity wafers manufactured with the float-zone method
- Hybridisation is a big limitation and risk for failure
 - Physical limitations on the pixel size due to physical dimensions of the bump bonds
 - Places extra requirements on sensor and FE chip planarity
 - Flip-chip process: alignment, compression, oxidation, surface condition, solder condition
 - Thermal stress acting on bump bonds during handling and operation
 - Novel bonding techniques being explored, e.g. Anisotropic Conductive Films (ACF), nano-wires

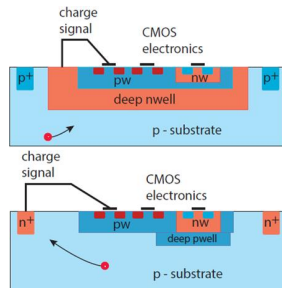
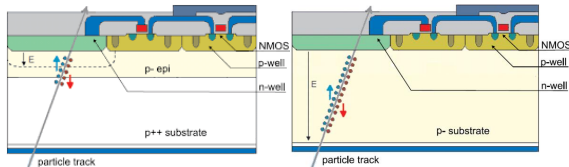




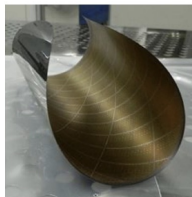
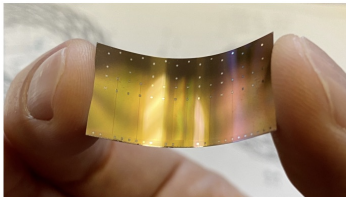
- Combine charge collection and FE electronics onto the same piece of silicon → Monolithic Active Pixel Sensor (MAPS)
- Using commercial HV-CMOS process on low-resistivity ($\sim 10\text{--}100\ \Omega\text{cm}$) Czochralski wafers - inexpensive "as cheap as chips", ideal to cover large areas with high resolution tracking detectors
- CMOS process is one of the most popular processes to manufacture analog and digital integrated circuits in silicon devices
- HV-CMOS allows the application of a relatively high voltage of $\sim 100\ \text{V}$, used in power devices
- Electronics are shielded by (nested) deep wells, can also act as collection electrode

- Terms like MAPS, HV-/CMOS sensors often used interchangeably
- MAPS: a general term, but sometimes indicates the standard process: usually on low resistivity wafers using an epitaxial layer for structures, slow charge collection, smaller pixels (e.g. $18\ \mu\text{m} \times 18\ \mu\text{m}$)
- DMAPS: (fully) Depleted MAPS, thinned so that breakdown voltage $>$ depletion voltage, high electric field throughout the bulk, fast charge collection (drift)
- HR-CMOS with high resistivity substrate behaves better but usually requires non-standard wafers

- Large fill factor
 - Usually large sensor capacitance
 - No/little low-field regions \rightarrow fast
 - Radiation tolerant
- Small fill factor
 - Usually use HR substrates
 - Large low-field regions \rightarrow slow
 - Less radiation tolerant

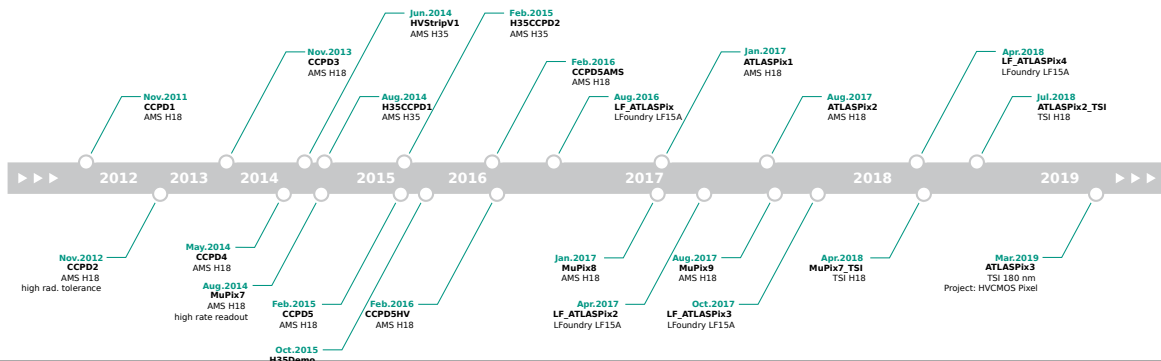


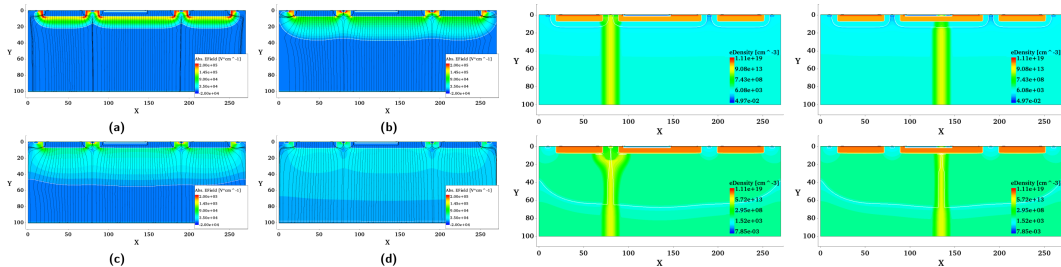
- Mimosa-26 (2009), used in EUDET-type beam telescopes
 - CMOS sensor in ams 350 nm technology
 - $18.4 \mu\text{m} \times 18.4 \mu\text{m}$ pixel pitch, rolling shutter readout
 - Slow: $115.2 \mu\text{s}$ integration time



- ALPIDE, will be used in ALICE ITS3 (2029)
 - 65 nm TowerJazz technology
 - Thinned down to $20\text{--}40 \mu\text{m}$ to be bent!
 - Radiation tolerant up to $1e13 \text{ 1MeV } n_{\text{eq}}/\text{cm}^2$

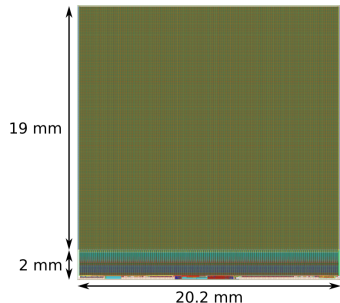
- ATLASPix3, proposed tracker for CEPC, same family as MuPix (Mu3e experiment), MightyPix (LHCb MightyTracker Upgrade)
- Name bears historical reasons: once a candidate for ATLAS ITk outer pixel layers!
- Output protocol Aurora 64b66b or 8b10b
- Mature DMAPS with large fill factor in ams/TSI 180 nm technology on $\sim 200 \Omega\text{cm}$ wafers
- Radiation hardness $\sim 2e15$ 1 MeV $n_{\text{eq}}/\text{cm}^2$



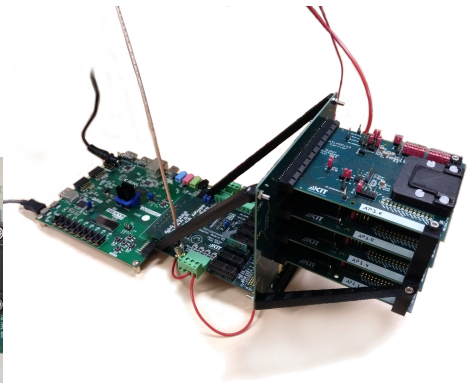


- Design process with help of TCAD (finite element) simulations
- Simulations of the fabrication process: details can be provided directly from the foundry, or using educated guess
- Faster simulations of the device structure only - more suited for HEP uses due to rather large structures (pixel vs transistor)
- Left: simulation of the electric field with different substrate resistivities with bias applied from the back
- Right: simulation of a MIP passing through at different positions for 20 Ωcm and 1000 Ωcm substrates

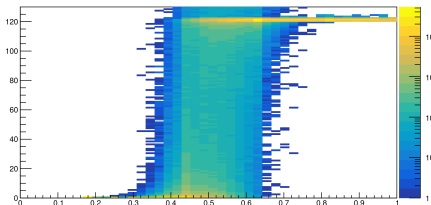
- Version 3 is the first full reticle-sized sensor for construction of multi-chip modules
- $20.2 \times 21 \text{ mm}^2$ reticle size, 132 columns \times 372 rows, $150 \times 50 \mu\text{m}^2$
- 3-bit threshold TDAC, 8-bit ToT, 10-bit time stamp
- Voltage regulators for shunt-LDO operation in serial power chains
- Column-drain readout with and without trigger (triggered and hit-driven)
- Configurable through serial, SPI bus or command line like RD53
- Data link 1.28 Gbit/s (64b66b) or up to 1.6 Gbit/s (8b10b)
- Low power \rightarrow less requirement on cooling: 160 mW/cm^2 (of which 120 mW/cm^2 is analog) - compared to 500 mW/cm^2 for ITk Pixel
- Low threshold: down to 400 e
- Low material budget: thinned to $150 \mu\text{m}$
- v3.1 with improvements (bias structure, time-walk) and trade-offs (shielding in signal injection) with minimal changes in the metal layers



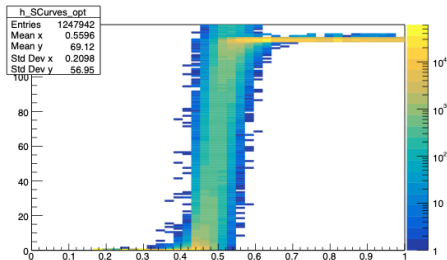
- Readout using GECCO (GEneric Configuration and COntrol) system (developed by KIT, Germany) for single chip, quad and telescope
- Diligent Nexys Video FPGA board + firmware
- Custom GECCO board (FMC-PCIe) with function card slots and power connection
- Single chip cards are PCIe cards
- Telescope-adapter card for up to 4 SCCs, all planes share the same HV and LV
- Qt-based software GUI



Threshold tuning

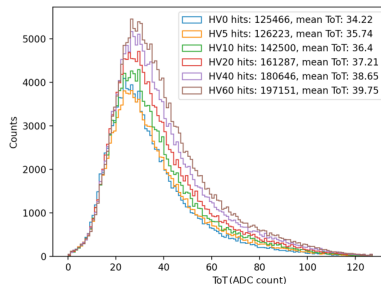
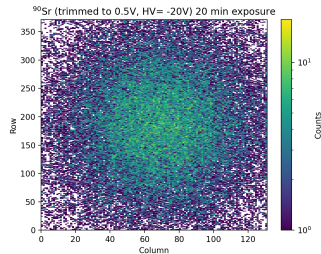


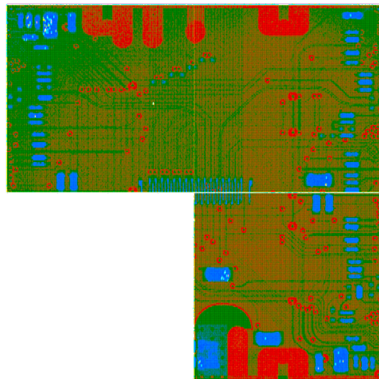
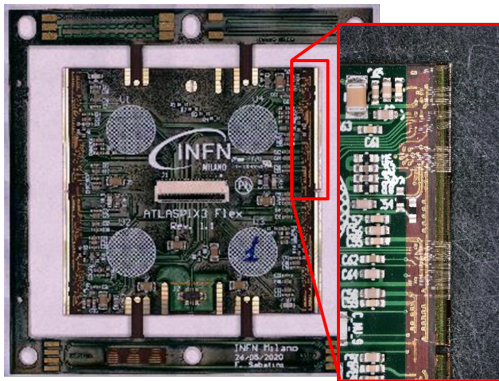
Untuned S-curves at TDAC=5 for row 40, $\sigma = 47$ mV



Tuned S-curves for row 40, $\sigma = 18$ mV

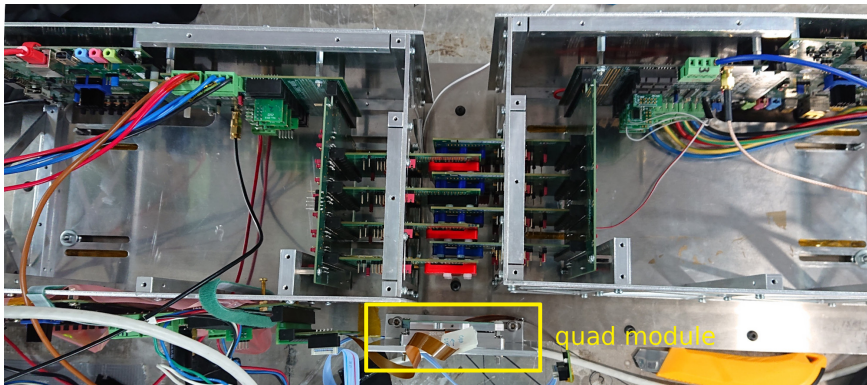
Source scan with Sr90



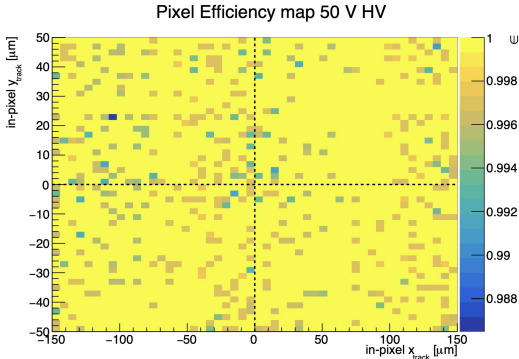
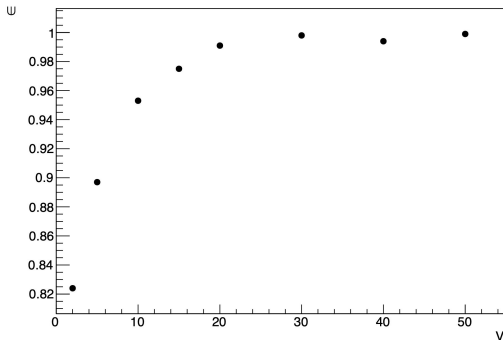


- Quad flex design inspired by ATLAS ITk Pixel
- Quad module assembly by hand and being tested in Milan
- Source measurement with x-ray (5 min with 15k–34k hits/s, untuned threshold)
- First quad in testbeam (display shows one chip in a quad)

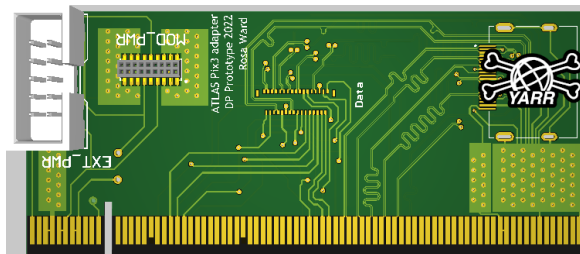
- Testbeam at DESY in 2022 using 6 GeV electron beam
- 2 arms in 2 standalone systems, biased at ~ 50 V (breakdown at ~ 60 V)
- Synchronisation provided by the primary system sending sync signal to the secondary
- Using hit-driven (untriggered) readout
- Interleaved arms with 1.27 cm distance between planes
- Quad module in the beam (bottom, in the pixel module carrier)



- Reconstruction and analysis with Corryvreckan (of one arm - synchronisation didn't work out)
- Not that straight-forward and required intensive debugging: crosstalk events, data corruption in hitwords (discarded)
- Total efficiency at 50 V is 99.56%



- Long journey of the ATLASPix chip family
- Mature and well-tested design for CEPC silicon tracker
- First experience with quad modules!
- Modified readout adapter card design exists with an additional DisplayPort - idea is to integrate into YARR



The measurements leading to these results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF)

- Recent [update](#) on a hybridisation vendor
- [CERN first module building experience](#)
- [On novel interconnections](#)
- [Performance of the EUDET-type beam telescopes](#)
- [High-Voltage CMOS Active Pixel Sensor](#)
- [Development of CMOS Sensors for High-Luminosity ATLAS Detectors](#)
- [ATLASPix3 Testbeam Results](#)
- [ATLASPix3 TB repo](#)
- [ATLASPix3 Manual](#)
- R. Schimassek, [Test results of ATLASPIX3 — A reticle size HVCMOS pixel sensor designed for construction of multi chip modules](#)
- Telescope public wiki:
https://git.scc.kit.edu/adl_publicsoftware/atlaspix3_public/-/wikis/Telescope-Revision-2-Wiki-Main-Page
- [Corryvreckan](#)